SDLS138

SN74LS19A, SN74LS24A SCHMITT-TRIGGER POSITIVE-NAND GATES AND INVERTERS WITH TOTEM-POLE OUTPUTS

JANUARY 1981 - REVISED MARCH 1988

- Functionally and Mechanically Identical to 'LS13, 'LS14, and 'LS132, Respectively
- Improved Line-Receiving Characteristics
- P-N-P Inputs Reduce System Loading
- Excellent Noise Immunity with Typical Hysteresis of 0.8 V

description

Each circuit functions as a NAND gate or inverter, but because of the Schmitt action, it has different input threshold levels for positivegoing (V_{T+}) and for negative-going (V_{T-}) signals. The hysteresis or backlash, which is the difference between the two threshold levels $(V_{T+} - V_{T-})$, is typically 800 millivolts.

These circuits are temperature-compensated and can be triggered from the slowest of input ramps and still give clean, jitter-free output signals.

logic symbols †

	SN74LS19A	
1A (1)	п	(2) 1V
2A (3)		(4) 2Y
3A (5)		(6) 3Y
4A (9)		(8) 4Y
5A (11)		(10) 5Y
6A (13)		1127 6Y

SN74LS24A 1A (1) & (3) 1Y 18 (2) 2A (4) 2B (5) 3A (9) 3B (10) 4A (12) 4A (13)

SN74LS19A . . . D, J, OR N PACKAGE (TOP VIEW)

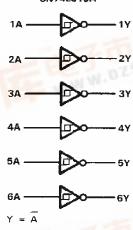
1A 🗌	1	V14 VCC	
TY	2	13 🗖 6A	
2A [3	12 🗀 6Y	
2Y 🗌	4	11 🛮 5A	
3A 🗌	5	10 5Y	
3Y 🗀	6	9 □ 4A	
GND 🗌	7	8 □ 4 Y	

\$N74LS24A . . . D, J, OR N PACKAGE (TOP VIEW)

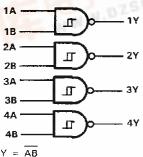
1A 🗌	1	U 14	Vcc
1B 🖂	2	13	_4B
17	3	12	4A
2A 🗌	4	- 11] 4Y
2B [5	10] 3B
2Y [6	9] 3A
GND 🗌	7	8] 3Y

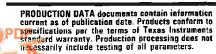
logic diagrams (positive logic)

SN74LS19A



SN74LS24A



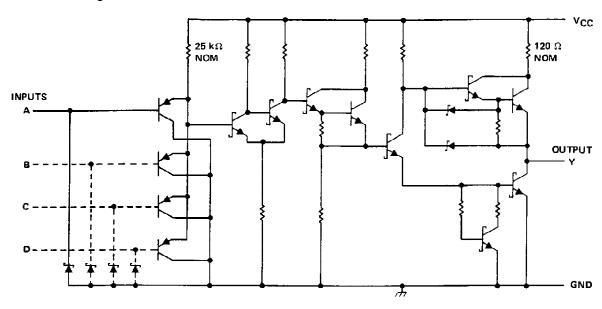


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[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

SN74LS19A, SN74LS24A SCHMITT-TRIGGER POSITIVE-NAND GATES AND INVERTERS WITH TOTEM-POLE OUTPUTS

schematic (each gate)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, VCC (see Note 1)	7 V
Input voltage	7 V
Operating free-air temperature range 0°C to 7	70°C
Storage temperature range -65°C to 15	$50^{\circ}C$

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, VCC	4.75	5	5.25	V
High-level output current, IOH			- 400	μΑ
Low-level output current, IQL			8	mA
Operating free-air temperature, T _A	0		70	°C

\$N74L\$19A, \$N74L\$24A SCHMITT-TRIGGER POSITIVE-NAND GATES AND INVERTERS WITH TOTEM-POLE OUTPUTS

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDIT	rions†	MIN	TYP#	MAX	UNIT	
V _T ,	V _{CC} = 5 V			1.65	1.9	2.15	V	
V _T _	V _{CC} = 5 V			0.75	1.0	1.25	V	
Hysteresis (V _{T+} - V _{T-})	V _{CC} = 5 V			0.4	0.9		٧	
VIK	V _{CC} = MIN,	i _I = → 18 mA	······		-1.5		V	
VoH	V _{CC} = MIN,	$V_{I} = V_{T-min}$	I _{OH} = -0.4 mA	2.7	3.4		V	
		11N, $V_1 = V_{T+max}$	$I_{OL} = 4 \text{ mA}$		0.25	0.4		
VOL VCC = N	ACC = MIIN'		I _{OL} = 8 mA		0.35	0.5	V	
IT+	Vcc = 5 V.	VI = VT+			-2	- 20	μΔ	
I _T _	V _{CC} = 5 V,				-5	- 30	μΑ	
11	$V_{CC} = MAX$	V _I = 7 V			0.1		mA	
liH	V _{CC} = MAX,	V _I = 2.7 V	<u> </u>			20	μА	
fil.	V _{CC} = MAX,	V _I = 0.4 V				- 50	μΑ	
los§	V _{CC} = MAX,	V _I = V _O = 0 V		- 20		- 100	mΑ	
1	V MAY		'LS19A		9.9	18		
ICCH VCC - MA	VCC - MAX,	- MAX, V _I - 0 V			6.6	12	mA	
1)/ MAY)(- 4 E)/	'LS19A		17	30		
ICCL	V _{CC} = MAX.	V = 4.5 V	'LS24A		11	20	mA	

[†] For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

switching characteristics, VCC - 5 V, TA - 25 °C (see Figure 1)

DADAMETED.	FROM	то	TEST CONDITIONS	SN74LS19A		SN74LS24A			UNIT	
PARAMETER (INPU	(INPUT)	NPUT) (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	ONII
tPLH	Any	Y	$R_1 = 2 k\Omega$. $C_1 = 15 pF$		13	20		13	20	ns
tpHL	Any	Υ	$R_L = 2 k\Omega$, $C_L = 15 pF$		18	30		25	40	ns

tpLH = Propagation delay time, low-to-high-level output

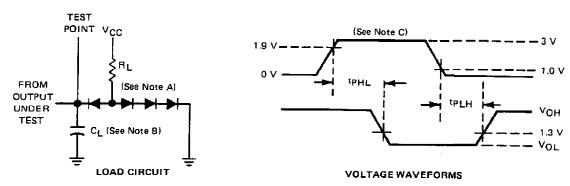
tPHL = Propagation delay time, high-to-low-level output



 $^{^{\}ddagger}$ All typical values are at V_{CC} = 5 V, T_A = 25 °C. $^{\$}$ Not more than one output should be shorted at a time, and the duration of the short-circuit should not exceed one second.

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. All diodes are IN3064 or equivalent.

B. C_L includes probe and circuit capacitance.

C. The generator characteristics are: PRR = 1 MHz, t_r = 15 ns, t_p = 6 ns, Z_o = 50 Ω .

FIGURE 1

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